## Investigation of the Dilution/Crystallization Dynamics of RDX and HMX by Microcalorimetry

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**Abstract** Three themokinetic equations describing the crystal grow th process and two relationships between the parameters and the constants of the kin-etic equations are derived. The total heat produced and the rate of heat production during the dilution/crystallization of RDX and HMX from dimethyl sulfoxide, cyclohexanone and nitric acid are measured using a Calvet microcalorimeter and a model RD-1 conduction calorimeter. The themokinetic data of crystal grow th processes of RDX and HMX are treated based on the derived equations and relationships. The results show that the exothem ic dilution/crystallization processes of RDX and HMX accord with the Burton-Cabrera-Frank dislocation theory.

Key words: single compound explosive; crystallization dynamics; RDX; HMX; dislocation theory

# 用微量热法研究 RDX 和 HM X 的稀释/结晶动力学

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摘 要: 导出了描述结晶生长过程的 3 个热动力学方程和这些动力学方程的参数与常数间的 2 个关系式。用 Calvet 微热量计测定了 RDX 和 HM X 从二甲基亚砜 环已酮和硝酸中的稀释/结晶总放热量和产热速率。用导出的方程和关系式处理了 RDX 和 HM X 的放热稀释/结晶生长过程的动力学数据。结果表明, RDX 和 HM X 的放热稀释/结晶过程 服从 Burton-Cabrera-Frank 位错理论。

关键词:单质炸药;结晶动力学;RDX;HMX;位错理论 中图分类号:TJ 55;TQ 564 文献标识码:A

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#### In troduction

RDX and HM X are two widely used nitram ine explosives and energetic ingredients of propellants In two previous notes<sup>[1,2]</sup>, the crystallization kinetics of RDX and HM X from DM SO and cyclohexanone, and that of HM X from HNO<sub>3</sub> were reported The aim of this work is to explore the adaptability of the themokinetic equations to the crystal grow th processes of RDX and HM X and obtaining the information about the interde-pendence between the parameters and the consta-nts of differ-**Received Date**: 2004- 03- 01 ent kinetic equations

### 1 Derivation of the kinetic equations of the crystal growth process

In order to analyze the kinetics of the crystal grow th process of RDX and HMX, the following general form of the crystal grow th process is used

A (aq)	—	A (s)	+	heat	
t = 0,	$C_0$	0, 0		0	(1)
t = t,	С	m, α		Н	(1)
t = ,	С	m, $\alpha = 1$		H	

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Biography: Hu Rong-zu (1938-), male, professor, research yields: them ochem istry and them al analysis

where, assuming that in forming the crystal A (s) from A (aq), C is the solute concentration in the so lution at time t (g/100 g so lvent). C is equilibrium staturation concentration (g/100 g solvent). m and  $\alpha$  are the mass and fraction of solid deposited during a certain time, respectively. H is the heat produced during a certain time t, and when t=0, C  $= C_0, m = 0, \alpha = 0 \text{ and } H = 0, \text{ when } t = 0, C = 0$ C, m = m,  $\alpha = \alpha = 1$  and H = H.

The relationship between the energy change (i e the heat produced) of a reacting system and the extent (i e mass or fraction or concentration) of the reaction (1) may be expressed as

$$\frac{C_0 - C}{C_0 - C} = \frac{0 - m}{0 - m} = \frac{0 - \alpha}{0 - \alpha} = \frac{0 - H}{0 - H}$$
(2)

From eq (2), we obtain

$$\alpha = \frac{H}{H}$$
(3)  
$$\frac{d\alpha}{dt} = \frac{1}{H} \frac{dH}{dt}$$
(4)

$$\frac{\mathrm{d}m}{\mathrm{d}t} = \left[\frac{m}{H}\right] \frac{\mathrm{d}H}{\mathrm{d}t} \tag{5}$$

and

$$\frac{C - C}{C_0 - C} = \begin{bmatrix} 1 - \frac{H}{H} \end{bmatrix}$$
(6)

Inserting eqs (3) and (4) into the differential kinetic equation (7) of the reaction of the *n*th order

$$\frac{\mathrm{d}\alpha}{\mathrm{d}t} = k \left(1 - \alpha\right)^n \tag{7}$$

The thermokinetic equations (8) and (9) are obtained:

$$\frac{\mathrm{d}H}{\mathrm{d}t} = H \quad k \left[ 1 - \frac{H}{H} \right]^n \tag{8}$$

and

$$\ln\left[\frac{1}{H}\left[\frac{dH}{dt}\right]\right] = \ln k + n \ln\left[1 - \left(\frac{H}{H}\right)\right]$$
$$i = 1, \ 2....L \qquad (9)$$

where H is the total heat produced (corre-sponding to the global area under the themokinetic curve);  $H_t$  is the heat produced in a certain time (corresponding to the partial area under the curve);  $dH_t/dt$  is the rate of heat production at time t; k and n are the rate constant and reaction order of the crystal grow th, respectively.

When 
$$\ln \left[ \frac{1}{H} \left[ \frac{dH}{dt} \right] \right]$$
 is plotted versus ln

 $\begin{bmatrix} 1 - \begin{pmatrix} H \\ H \end{bmatrix} \end{bmatrix}$  by the least-squares method, this gives the value of n from the slope and k from the intercept.

Equation (8) is known as the general form describing the crystal grow th process

A ccording to the Burton-Cabrera-Frank (BCF) dislocation theory<sup>[3]</sup>, for relatively high supersaturation, the rate of crystal grow that time t, dm/dt may be expressed as

$$\frac{\mathrm{d}m}{\mathrm{d}t} = km \quad (C - C) \tag{10}$$

The combination of eqs (5), (6) and (10)gives

$$\frac{\mathrm{d}H}{\mathrm{d}t} = kH \quad (C_0 - C) \left[ 1 - \frac{H}{H} \right] = k_1 \left[ 1 - \frac{H}{H} \right]$$
(11)

here 
$$k_1 = kH (C_0 - C)$$
 (12)

If  $C_0 > > C$ , we have

$$\frac{\mathrm{d}H}{\mathrm{d}t} = kH \quad C_0 \left[ 1 - \frac{H}{H} \right] = k_2 \left[ 1 - \frac{H}{H} \right] \quad (13)$$

where

re  $k_2 = kH C_0$  (14) when  $\begin{pmatrix} dH \\ dt \end{pmatrix}_i$  is plotted versus 1-  $\begin{pmatrix} H \\ H \end{pmatrix}_i$  by the least-squares method, this gives the values of

 $k_2$  and a in the equation (15)

$$\frac{\mathrm{d}H}{\mathrm{d}t} = k_2 \left[ 1 - \frac{H}{H} \right] + a \tag{15}$$

If equation (10) is written as

$$\frac{\mathrm{d}m}{\mathrm{d}t} = km \quad (C - C) + b \tag{16}$$

The equation (17) is obtained by combining eqs (5), (6) and (16)

$$\frac{dH}{dt} = \frac{dm}{dt} \left( \frac{H}{m} \right) = \frac{H}{m} \left[ km \quad (C - C \quad) + b \right]$$

$$= \frac{H}{m} \left[ km \quad (C_0 - C \quad) \left( 1 - \frac{H}{H} \right) + b \right]$$

$$= H \quad k \left( C_0 - C \quad) \left( 1 - \frac{H}{H} \right) + \frac{bH}{m}$$

$$= H \quad k C_0 \left( 1 - \frac{H}{H} \right) + \frac{bH}{m} \left( C_0 > > C \quad \right)$$
(17)

Comparing eq (15) with eq (17), two relationships [eqs (18) and (19)] are obtained

$$k = k_2 / H \quad C_0 \tag{18}$$

(19)

b = Otn /H

Equations (18) and (19) relate k to  $k_2$  and b to a, respectively.

If the values of the constants a and b are small in comparison with those of  $k_2$  and k, the kinetics of the crystal growth processes can be expressed by eqs (10) and (13).

Equations (10) and (13) are known as the thermokinetic equations of the crystal grow th process Equation (13) is only an especial example (n = 1) of equation (8).

#### 2 Experimental

#### 2 1 Materials

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RDX and HM X used as solutes were prepared by our institute The RDX contained no detectable HM X, and HM X contained no detectable RDX. Their purities were more than 99, 9%. DM SO (m. p. 16 5~ 19 ;  $r_4^{20} = 1.098$ ~ 1.106) and cyclohexanone (b p. 154 0~ 156 0 ;  $r_D^{20} = 1.4500$ ~ 1. 4510) used as solvents are of chemical and analytical purity respectively. The concentration of HNO 3 used as solvent was 95 68%. A 50 10% DM SO-H2O mixture and n-C7H16/CCl4 (1: 1, V/V) are used as diluents, where H2O is twice distilled water; n-C7H16 (b p. 96 5~ 98 5 ;  $r_4^{20} = 0.683$ ~ 0 686) and CCl4 (b p. 75 5~ 77.5 ;  $r_4^{20} = 1.591$ ~ 1.597) are of chemical purity.

#### 2 2 Experimental equipment and conditions

A ll measurements at 30 are made using a Calvet microcalorimenter, type BT 215 from SE-TARAM, France, which has a sensitivity of 66 5  $\mu$ V · mW<sup>-1</sup> and is equipped with two 15 ml vessels A ll measurements at 34 are made using a conduction calorimenter, type RD-1 from Sichuan U niversity, with a precision of ± 0 5% and equipped with two 60 ml vessels The microcalorimeter is calibrated by the Joule effect and the calibration is repeated after each experiment The precision of enthalpy measur-ement is 2%. The device used for the study of the crystallization kinetics is shown in Fig 1. (1. thin glass bulb containing diluent; 2 polyt-etrafluoroethylene tube; 3 glass tube containing RDX or HMX solution; 4 silicon rubber cover; 5 calorimetric cell; 6 glass rod On depressing the rod, the bottom of the glass bulb is broken, and the solution and diluent m ix together in the tube).







Fig 2 Typical themogram obtained during dilution/crystallization



Fig 3 Block diagram of the process of studying dilution/crystallization kinetics

A typical schematic themogram obtained during the dilution and crystallization is shown in Fig 2, and is obtained by the testing and computing method presented as a block diagram in Fig 3.

In Fig 3,  $(dH/dt)_{1i}$  is the rate of total heat

production at time t, including the rate of the heat of m ixing produced between solvent and diluent,  $(dH/dt)_{2i}$ , and the rate of the heat of crystallization of the crystal,  $(dH/dt)_{3i}$  at time t; and H<sub>1i</sub> is the total heat produced during a certain time, including the heat of m ixing produced between solvent and diluent, H<sub>2i</sub>, and the heat of crystallization by the crystal during a certain time

The themograms obtained under the same conditions overlapped with each other, indicating that the reproducibility of tests was satisfactory.

#### 3 **Results and discussion**

To verify the reliability of eqs (8), (15) and (16) and obtain information about the kinetic parameters and the constants of RDX and HMX, the original themokinetic data tabulated in Table 1 are fitted to the eqs (8), (15) and (16) by the linear least-squares method Results obtained, including the total heat produced, the reaction order (n), the rate constants  $(k_2 \text{ and } k)$  during the crystallization of RDX and HMX from DM SO and cyclohexanone at 30 and that of HMX from HNO<sub>3</sub> at 34 , and the constants (a and b) in eqs (15) and (16), are shown in Table 2

From Tables 1 and 2, the following obser-vations can be made:

(1) The crystal grow th processes of RDX and
 HM X are exotherm ic The exotherm ic process may
 be expressed by the isothermal differential kinetic
 equation (8)

(2) BCF model [eq (13)] is only an especial example (n=1) of the general form [eq (8)] of the crystal grow th process

(3) Because  $k_2 > d$  in [eq (15)] and k > bin [eq (16)], describing the kinetics of the crystal grow th processes of RDX and HM X by the eqs (15) and (16) are tenable This indicates that the crystal grow th processes of RDX and HM X from DM SO and cyclohexanone and that of HM X from HNO<sub>3</sub> without seeds of HM X accords with the BCF dislocation theory.

(4) In our experimental conditions, the crystal grow th process of HM X from HNO<sub>3</sub> with seeds of HM X is out of accord with the BCF dislocation theory.

	Expe	erimental conditions N	o. 1	Experimental conditions No. 2			
Tempe 30	So lu te RDX (0_0084g)	SolventSeedDM SO50(0 0250g)	D iluen t 1% DM SO <del>-</del> H <sub>2</sub> O (0 6896g)	Tempe         Solute           30         RDX           (0.0084	Solvent Seed DM SO RDX g) (0 0250g) (0 4000g)	D iluen t 50 1% DM SO -H 20 ) (0 6896g)	
	t/s	$(dH/dt)_i/10^4 (J \cdot s^{-1})_i$	$(H_t)_i/10^2 J$	t/s	$(dH/dt)_i/10^4 (J \cdot s^{-1})$	$(H_{t})_{i}/10^{2}$ J	
	210	6 991	2 761	210	10 00	15.69	
	240	6 255	5. 146	240	8 841	18 58	
	270	6 092	7. 155	270	8 251	21. 13	
	300	5. 573	9. 372	300	7. 372	23 47	
	330	5 196	11.00	330	6 640	25 61	
	360	4 749	12 84	360	6 050	27. 61	
	390	4 297	14.69	390	5. 460	29.54	
	420	4 134	16 15	420	5. 012	30 96	
	450	3 686	17.61	450	4.711	32 76	
	480	3 655	19.08	480	4 263	34 18	
	510	3 502	20 17	510	4 100	35 19	
	540	3 197	21. 25	540	3 937	36 40	
	570	3 033	22 38	570	3 494	37. 61	
	600	2 870	23 47	600	3 188	38 66	

Table 1 Themokinetic data of the crystal grow th processes of RDX and HMX

	Exp	erimental conditions N	Jo. 1	Experimental conditions No. 2			
Tempe	So lu te	Solvent Seed	Diluent	Tempe Solute	e Solvent Seed	Diluent	
30	RDX (0_0084g)	DM SO 5 (0 0250g)	0 1% DM SO H 2O (0 6896g)	30 RDX (0 0084	DM SO RDX 5 g) (0.0250g) (0.4000g)	0 1% DM SO -H 2O (0 6896g)	
	t/s	$(dH/dt)_{i}/10^{4} (J \cdot s^{-1})_{i}$	<sup>1</sup> ) $(H_{t})_{i}/10^{2}$ J	t/s	$(dH/dt)_{i}/10^{4}(J \cdot s^{-1})$	$(H_{t})_{i}/10^{2} J$	
	630	2 506	24. 31	630	3 025	39.66	
	660	2 544	25.48	660	2 720	40 67	
	690	2 523	26 40	690	2 845	41. 51	
	720	2 218	27. 15	720	2 540	42 17	
	750	2 054	28 07	750	2 234	42 97	
	780	1. 891	28 79	780	2 075	43 81	
	810	1. 728	29.33	810	2 054	44 21	
	840	1. 565	30 25	840	1. 895	44.65	
		0	42 72		0	44 73	
	Exp	erimental conditions N	10. 3	OE	Experimental conditions N	lo. 4	
Tempe	So lu te	Solvent Seed	Diluent	Tempe Solute	e Solvent Seed	Diluent	
30	HM X (0 0022g)	cyclohexanon HM X $(0, 1000g)(0, 4771g)$	$1^{-}C_{7}H_{16}/CC_{4}(1:1)$ (0.9555g)	34 HM X (0.3648	HNO <sub>3</sub> (2 8685g)	H <sub>2</sub> O (0. 7910g)	
	t/s	$(dH/dt)_i/10^5 (J \cdot s)$	<sup>1</sup> ) ( <i>H</i> <sub>t</sub> ) $i/10^{2}$ J	t/m in	$(dH/dt)_i/(J \cdot m in^{-1})$	$(H_t)_i/J$	
	210	118 2	22 18	1. 25	19.54	6 109	
	240	98 24	26 57	1. 50	19. 63	10 79	
	270	88 20	30 59	2 00	19.87	19. 25	
	300	80 75	34.06	2 25	21. 34	25.44	
	330	68 16	36 78	2 50	15.77	29.62	
	360	58 12	39.16	2 75	13 81	33 30	
	390	46 69	41.34	3 00	13 43	37. 28	
	420	40 96	43. 18	5.50	6 987	62 59	
	450	35 19	44.60	6 50	5. 565	68 53	
	480	26 61	44.73	7.50	4 770	74 27	
	510	22 30	46 78	8 50	3 138	78 58	
	540	17.99	47.66	10 5	2 887	83 89	
	570	12 26	48 37	12 5	2 092	87.70	
	600	7.949	48 91	13 5	1. 674	89.62	
	630	3 598	49. 21	14.5	1 297	90 88	
		0	49.33		0	93 64	
	Exp	erimental conditions N	No. 5	Experimental conditions No. 5			
Tempe 34	So lute HM X (0, 3684g)	Solvent Seed HNO <sub>3</sub> HM X (2, 8685g)(0, 2089g)	D iluent H $_{2}O$ (0, 7910g)	Tempe Solute 34 HM X (0.3684	e Solvent Seed HNO <sub>3</sub> HM X (2,8685g)(0,2089g)	D iluent H $_{2}O$ (0, 7910g)	
	t/m in	$(dH/dt)_i/(I \cdot m in^{-1})_i$	$(H_{t})_{i}/J$	( <u>u</u> 2004	$(dH/dt)/(I \cdot m in^{-1})$	$(H_t)_i/J$	
	1.00	42 63	30 54	5. 50	5. 397	77. 65	
	1. 25	24 02	38 45	7.50	3 556	83 81	
	1.50	14 39	43 39	9.50	2 176	88 70	
	1.75	13 22	46 40	12 5	1. 297	94.14	
	2 00	9. 623	49.54		0	102 4	
	2 75	8 326	56 44				
 34	600 630 Exp So lu te HM X (0 3684g) t/m in 1 00 1 25 1 50 1 75 2 00 2 75	7. 949 3. 598 0 erim ental conditions N Solvent Seed HNO <sub>3</sub> HM X (2. 8685g)(0. 2089g) ( $dH/dt$ ) $i/(J \cdot m in)$ 42. 63 24. 02 14. 39 13. 22 9. 623 8. 326	$ \begin{array}{r}     48 91 \\     49 21 \\     49 33 \\ \hline     49 33 \\ \hline     10 5 \\ \hline     D iluent \\     H D \\     (0 7910g) \\ \hline     1 (H_{i})_{i}/J \\ \hline     30 54 \\ \hline     38 45 \\ \hline     43 39 \\ \hline     46 40 \\ \hline     49 54 \\ \hline     56 44 \\ \hline \end{array} $	13 5 14 5 Tempe Solute 34 HM X (0 3684 t/m in 5 50 7 50 9 50 12 5	1. 674 1. 297 0 Experimental conditions N e Solvent Seed HNO <sub>3</sub> HM X lg) (2.8685g)(0.2089g) (dH /dt) $i/(J \cdot m in^{-1})$ 5.397 3.556 2.176 1.297 0	$   \begin{array}{r}       89, 62 \\       90, 88 \\       93, 64 \\       10, 5 \\       D iluent \\       H: O \\       (0, 7910g) \\       (H_{-}); /J \\       77, 65 \\       83, 81 \\       88, 70 \\       94, 14 \\       102, 4 \\   \end{array} $	

Table 1 Them okinetic data of the crystal grow th processes of RDX and HMX

Table 2 Total heat produced and crystal glow in Kinetics of KDX and him X									
т/	H / (J · g <sup>-1</sup> )	$\frac{\mathrm{d}H}{\mathrm{d}t} = H  k \left[ 1 - \frac{H}{H} \right]^n$		$\frac{\mathrm{d}H}{\mathrm{d}t} = k_2 \left[ 1 - \frac{H}{H} \right] + a$			$\frac{\mathrm{d}H}{\mathrm{d}t} = km  (C - C) + b$		
		$k \times 10^3 / s^{-1}$	<sup>1</sup> n	r	$k_2 \times 10^4 / (J \cdot s)$	<sup>1</sup> ) $a \times 10^{5} / (J \cdot s)$	$s^{-1}$ ) r	$k \times 10^3 / s^{-1}$	$b \times 10^{6} / (g \cdot s^{-1})$
30	50 86	1.74	1. 22	0 997	8 09	- 8 01	0 997	1. 60	- 1.57
30	53 25	1. 68	0 307	0 984	12 0	16 8	0 996	4.47	3 15
30	224 2	3 23	0 640	0 996	20 3	11.0	0 991	19.7	0 049
34	256 7	3 68	0 844	0 986	3810	400	0 981	0 408	15.6
34	268 1	5.75	1. 38	0 958	7710	- 10500	0 822	0 775	- 392

Table 2 Total heat produced and crystal grow th kinetics of RDX and HMX

(5) W ith the addition of seed crystals of RDX and HMX, the value of k in eq. (16) is larger than that of k without seeds. This shows that the total number of nuclei in the seeded solution is greater than that in unseeded solution.

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# 2005 年火炸药新技术学术研讨会征文通知 (补充通知)

为促进火炸药技术创新与可持续发展,为实现我军武器装备的信息化作出贡献,经总装备部火炸药技术 专业组、火炸药燃烧国防科技重点实验室、中国兵工学会火炸药专业委员会协商,决定共同主办"2005 年火 炸药新技术学术研讨会",并委托中国兵器工业第二O四研究所负责承办。会议将邀请著名专家、学者做专 题报告,并就近期国内外火炸药行业发展中的新技术、新成果、应用研究等内容进行交流。欢迎各位专家、学 者、工程技术人员、高校师生积极参加。

1. 学术讨论会主题: 火炸药技术创新与可持续发展

2 征文内容: (1)高能量密度化合物的合成与应用; (2)新型含能材料合成与应用; (3)新型功能材料合成与应用; (4)新型火炸药技术; (5)火炸药数值模拟仿真技术; (6)火炸药装药新技术; (7)火炸药先进制造技术; (8)火炸药理化分析与测试新技术; (9)火炸药安全性与可靠性新技术; (10)火炸药燃烧与爆炸新技术; (11)火炸药应用基础创新研究; (12)新概念火炸药及其应用。

3 **征文要求**: (1)会议前拟出版会议论文集, 凡内容符合征文要求的论文均可投稿。所撰写论文应观点明 确、论据可靠、文字流畅、插图清楚, 每篇字数不超过 5000 字(含论文摘要、关键词、参考文献); (2)论文编写 遵循我国正式出版物上科技论文的标准规范要求, 用Word2000 排版; (3)页面打印格式: A 4 纸激光打印、版 心 15 × 21cm (具体要求见附页); (4)保密审查由撰写论文单位把关; (5)论文需要递交激光打印稿及电子稿, 请通过加密网或机要方式寄送至 204 研究所; (6)论文征文截至日期: 2005 年 3 月 31 日。

- 4 会议暂定地点、时间: 湖南长沙 2005 年 5~ 6 月
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